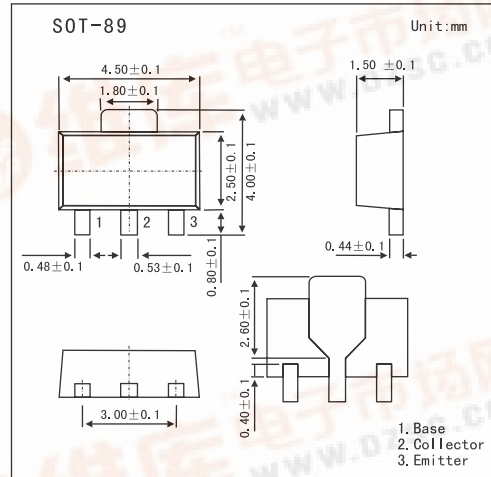


SMD Type Transistors

PNP Silicon Power Transistor  
2SB772

■ Features

- Low saturation voltage.  
 $V_{CE(sat)} \leq -0.5$  (@  $I_c = -2A, I_B = -0.2A$ )
- Excellent  $h_{FE}$   
 $h_{FE}: 60$  to  $400$  (@  $V_{CE} = -2V, I_c = -1A$ )



■ Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Collector to base voltage	$V_{CBO}$	-40	V	
Collector to emitter voltage	$V_{CEO}$	-30	V	
Emitter to base voltage	$V_{EBO}$	-5	V	
Collector current	$I_c$	-3	A	
Collector Power dissipation	$P_c$	$T_a = 25^\circ C$	1.0	W
		$T_c = 25^\circ C$	10	W
Junction temperature	$T_j$	150	$^\circ C$	
Storage temperature range	$T_{stg}$	-55 to +150	$^\circ C$	

\*  $PW \leq 350\mu s, \text{duty cycle} \leq 2\%$ .

■ Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_c = -10 \text{ mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -100 \mu A, I_c = 0$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -30 \text{ V}, I_E = 0$			-1.0	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_c = 0$			-1.0	$\mu A$
DC current gain *	$h_{FE}$	$V_{CE} = -2.0 \text{ V}, I_c = -1.0 \text{ A}$ *	60	160	400	
Collector saturation voltage *	$V_{CE(sat)}$	$I_c = -2 \text{ A}, I_B = -0.2 \text{ A}$		-0.3	-0.5	V
Base saturation voltage *	$V_{BE(sat)}$	$I_c = -2 \text{ A}, I_B = -0.2 \text{ A}$		-1.0	-2.0	V
Output capacitance	$C_{ob}$	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		55		pF
Transition frequency	$f_T$	$V_{CE} = -5.0 \text{ V}, I_E = -0.1 \text{ A}, f = 10 \text{ MHz}$		80		MHz

\* Pulsed:  $PW \leq 350 \mu s, \text{duty cycle} \leq 2\%$

■  $h_{FE}$  Classification

Rank	R	Q	P	E
$h_{FE}$	60~120	100~200	160~320	200~400

